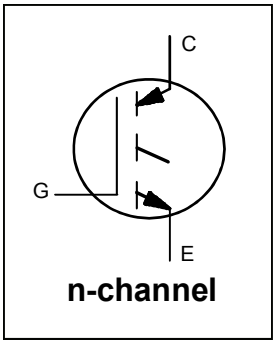
International
IOR Rectifier
AN INFINEON TECHNOLOGIES COMPANY

IRGC4275B

INSULATED GATE BIPOLAR TRANSISTOR



Features
- Low $V_{CE\ (ON)}$ Trench IGBT Technology
- Low Switching Losses
- Maximum Junction Temperature 175 °C
- Short Circuit Rated
- Square RBSOA
- Positive $V_{CE\ (ON)}$ Temperature Coefficient
- Tight Parameter Distribution
- Integrated Gate Resistor

G	C	E
Gate	Collector	Emitter

Benefits
- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low $V_{CE\ (ON)}$ and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Easier Paralleling with Integrated Gate Resistor

Applications
- Industrial Motor Drives
- Inverter
- UPS
- Welding

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRGC4275B	Die on Film	Wafer	1	IRGC4275B

Mechanical Parameters

Die Size	10 x 10	mm^2
Minimum Street Width	75	µm
Emiter Pad Size (Included Gate Pad)	See Die Drawing	mm^2
Gate Pad Size	1.0 x 1.717	
Area Total / Active	100/ 81.89	
Thickness	70	µm
Wafer Size	150	mm
Flat Position	0	Degrees
Maximum-Possible Chips per Wafer	136pcs.	
Passivation Front side	Silicon Nitride	
Front Metal	Al, Si (4µm)	
Backside Metal	Al (1kA°), Ti (1kA°), Ni (4kA°), Ag (6kA°)	
Die Bond	Electrically conductive epoxy or solder	
Reject Ink Dot Size	0.25 mm diameter minimum black	

Maximum Ratings

	Parameter	Max.	Units
V_{CE}	Collector-Emitter Voltage, T_J=25°C	650	V
I_C	DC Collector Current	①	A
I_{LM}	Clamped Inductive Load Current ④	800	A
V_{GE}	Gate Emitter Voltage	± 20	V
T_J, T_{STG}	Operating Junction and Storage Temperature	-40 to +175	°C

Static Characteristics (Tested on wafers) . T_J=25°C

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	650	——	——	V	V_{GE} = 0V, I_C = 100µA ⑤
$V_{CE(sat)}$	Collector-to-Emitter Saturated Voltage	——	1.6	1.9		V_{GE} = 15V, I_C = 200A, T_J = 25°C
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	5.5	——	7.7		I_C = 6.6mA, V_{GE} = V_{CE}
I_{CES}	Zero Gate Voltage Collector Current	——	1.0	20	µA	V_{CE} = 650V, V_{GE} = 0V
I_{GES}	Gate Emitter Leakage Current	——	——	± 600	nA	V_{CE} = 0V, V_{GE} = ±20V
$R_{G\ INTERNAL}$	Internal Gate Resistance	1.6	2.0	2.4	Ω	

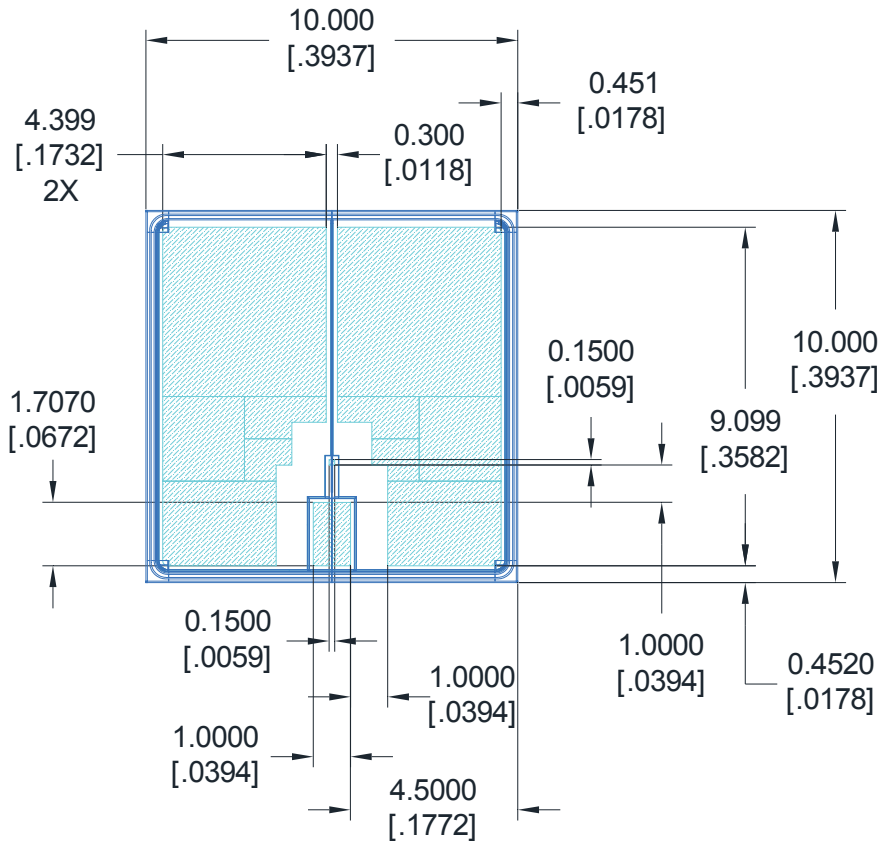
Electrical Characteristics (Not subject to production test- Verified by design/characterization)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{CE(sat)}$	Collector-to-Emitter Saturated Voltage	——	1.6	1.9	V	V_{GE} = 15V, I_C = 200A , T_J = 25°C
		——	2.0	——		V_{GE} = 15V, I_C = 200A , T_J = 175°C
SCSOA	Short Circuit Safe Operating Area	5.5	——	——	µs	V_{GE} = 15V, V_{CC} = 400V, ② R_G = 5.0Ω, V_P ≤ 600V, T_J = 150°C
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 175°C, I_C = 800A V_{CC} = 480V, Vp ≤ 600V Rg = 5.0Ω, V_{GE} = +20V to 0V
C_{iss}	Input Capacitance	——	12940	——	pF	V_{GE} = 0V
C_{oss}	Output Capacitance	——	650	——		V_{CE} = 30V
C_{rss}	Reverse Transfer Capacitance	——	340	——		f = 1.0MHz
Q_g	Total Gate Charge (turn-on)	—	380	—	nC	I_C = 200A ⑥
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	140	—		V_{GE} = 15V
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	170	—		V_{CC} = 400V

Switching Characteristics (Inductive Load-Not subject to production test-Verified by design/characterization)

	Parameter	Min.	Typ.	Max.	Units	Conditions ③
$t_{d(on)}$	Turn-On delay time	—	130	—	ns	I_C = 200A, V_{CC} = 400V
t_r	Rise time	—	330	—		R_G = 5.0Ω, V_{GE} = 15V
$t_{d(off)}$	Turn-Off delay time	—	280	—		T_J = 25°C
t_f	Fall time	—	140	—		
$t_{d(on)}$	Turn-On delay time	—	115	—		I_C = 200A, V_{CC} = 400V
t_r	Rise time	—	330	—		R_G = 5.0Ω, V_{GE} = 15V
$t_{d(off)}$	Turn-Off delay time	—	330	—		T_J = 175°C
t_f	Fall time	—	160	—		

Die Drawing



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
2. CONTROLLING DIMENSION: INCHES
3. DIE WIDTH AND LENGTH TOLERANCE: -0.0508 [.002]
4. DIE THICKNESS = 0.070 [.00276]

REFERENCE: IRGC4275B
IRGC4275F

Notes:

① The current in the application is limited by T_{JMax} and the thermal properties of the assembly.
② Not subject to production test- Verified by design / characterization.
③ Values influenced by parasitic L and C in measurement.
④ V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 66µH, R_G = 5.0Ω.
⑤ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely
⑥ Die Level Characterization.

Additional Testing and Screening

For Customers requiring product supplied as Known Good Die (KGD) or requiring specific die level testing, please contact your local IR Sales

Shipping

Sawn Wafer on Film. Please contact your local IR sales office for non-standard shipping options

Handling

- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Product must be handled only in a class 10,000 or better-designated clean room environment.
- Singulated die are not to be handled with tweezers. A vacuum wand with a non-metallic ESD protected tip should be used.

Wafer/Die Storage

- Proper storage conditions are necessary to prevent product contamination and/or degradation after shipment.
- Note: To reduce the risk of contamination or degradation, it is recommended that product not being used in the assembly process be returned to their original containers and resealed with a vacuum seal process.
- Sawn wafers on a film frame are intended for immediate use and have a limited shelf life.

Further Information

For further information please contact your local IR Sales office. http://die.irf.com

Revision History

Date	Comments
07/02/2015	• Updated IFX logo on all pages • Removed Vcesat @ I_C =20A, V_{GE} = 15V on page 2. • Added Vcesat @ I_C = 200A, V_{GE} = 15V on page 2.

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To contact International Rectifier, please visit http://www.irf.com/whoto-call/

